

PATENT

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**REVOCATION OF POWER OF ATTORNEY,
NEW POWER OF ATTORNEY BY ASSIGNEE AND
CHANGE OF CORRESPONDENCE ADDRESS**

Sir:

Assignee hereby revokes all powers of attorney previously granted with respect to the patent applications identified in Appendix A, and appoints the firm of Myers Bigel Sibley & Sajovec:

Customer No. 20792

as its attorney, with full power of substitution and revocation to transact all business in the Patent and Trademark Office in connection therewith.

Please direct all communications as follows:

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Assignee hereby elects under 37 C.F.R. § 3.71 to prosecute the patent applications listed in Appendix A.

The undersigned Assignee hereby certifies that Samsung Electronics Co., Ltd. is the assignee of the entire right, title, and interest in the patent applications identified in Appendix A by virtue of a chain of title from the inventor(s) of the patent application identified to Hewlett-Packard Development Company, L.P. and then to the current assignee as shown in Appendix A.

The documents in the chain of title of the patent application identified above have been reviewed and, to the best of undersigned's knowledge and belief, title is in the assignee identified above.

The undersigned (whose title is supplied below) is empowered to sign this certificate on behalf of the Assignee.

I hereby declare that all statements made herein of my own knowledge are true, and that all statements made on information and belief are believed to be true; and further, that these statements are made with the knowledge that willful false statements, and the like so made, are punishable by fine or imprisonment, or both, under Section 1001, Title 18 of the United States Code, and that such willful false statements may jeopardize the validity of the application or any patent issuing thereon.

Samsung Electronics Co., Ltd.

By: Jeong-Taek Kong
Jeong-Taek Kong

Title: Senior Vice President of IP Team

Date: Aug. 23, 2007

APPENDIX A

In re	Serial No.	Filed	Title	Assignment Recorded	Res.	Frame	Att. Dkt. No.
Adelmann	10/62,632	07/17/03	Assisted Memory Device with Integrated Cache	Samsung 07/18/03	014138 0051	5649-2218	
Smith	10/743,662	12/22/03	MRAM with Controller	Samsung 07/26/07	015613 0070	5649-2215	
Perner	11/252,143	10/17/05	System and Method for Reading a Memory Cell	Samsung 07/26/07	014841 0615	5649-2219	
Anthony	11/021,268	12/23/04	Magnetic Memory Device and Methods for Making Same	HPDC 01/27/04	015611 0239	5649-2220	
Jedwab	10/722,918	11/26/03	Magnetic Memory which Compares Compressed Fault Maps	Samsung 07/26/07	014930 0571	5649-2220	
Selek	10/700,203	11/03/03	Magnetic Memory	Samsung 07/26/07	015612 0436	5649-2221	
Pline	10/725,355	12/02/03	Data Storage System with Error Correction Code and Replaceable Defective Memory	HPC 02/10/03	013737 0985	5649-2221	
Spencer	11/203,755	8/15/05	Method of Packaging Magnetic Memory	HPDC 06/18/03	013776 0928	5649-2222	
Lee	10/698,501	10/31/03	Heating MRAM Cells to Ease State Switching	Samsung 07/26/07	015611 0807	5649-2222	
Stobbs	10/631,404	07/30/03	Magnetic Shielding for Magnetic Random Access Memory	Samsung 07/26/07	013801 0631	5649-2225	
Tausig	10/914,255	08/09/04	Silver Island Anti-Fuse	HPC 03/04/03	014061 0492	5649-2225	
Sharma	10/144,927	04/16/03	Optical Signal Transmission Transducer	HPC 06/20/03	015611 0853	5649-2226	
Perner	11/264,539	11/01/05	Controllably Connectable Strings of MRAM Cells	HPDC 02/09/04	014320 0883	5649-2226	
Nickel	10/315,748	12/10/02	Thermally-Assisted Switching of Magnetic Memory Elements	Samsung 07/26/07	015612 0754	5649-2227	
Lee	10/692,612	10/24/03	A Method of Making a Magnetic Tunnel Junction Device	HPDC 09/11/03	013891 0927	5649-2231	
Nauka	10/698,717	10/31/03	Data Storage Device Including Conductive Probe and Ferroelectric Storage Medium	Samsung 07/26/07	015613 0864	5649-2234	
Perner et al.	10/698,896	10/31/03	Multi-Sample Read Circuit Having Test Mode of Operation	HPDC 03/25/04	015678 0222	5649-2235	
Nickel	10/733,089	12/11/03	Using Sense Lines to Thermally Control the State of an MRAM	Samsung 07/26/07	014817 0794	5649-2236	
				Samsung 07/26/07	019613 0913		

APPENDIX A

Intre:	Serial No.:	Filed:	Title:	Assignment Recorded:	Res:	Frame:	Aut. Dist. No.:
Nickel	10/934,922	09/02/04	Thin Film Device and a Method of Formation Thereof	HPDC 09/02/04 Samsung 07/26/07	01961.0240 01961.0222		5649-2237
Perner	10/934,243	09/03/04	Method and Apparatus for Multi-Plane MRAM	HPDC 09/03/04 Samsung 07/26/07	01961.0570 01961.0064		5649-2238
Zhang	10/721,574	11/25/03	Molecular Optoelectronic Memory Device	HPDC 03/31/04 Samsung 07/26/07	014478.0520 01961.0206		5649-2239
Sharma	11/285,991	11/23/05	Multi-Layered Magnetic Memory Structures	HPDC 11/23/05 Samsung 07/26/07	017281.0685 01961.0342		5649-2240
Sharma	11/118,828	04/29/05	Process for Forming Magnetic Memory Structures	HPDC 04/29/05 Samsung 07/26/07	016527.0690 01961.0287		5649-2241
Sharma	11/286,245	11/23/05	Multi-Layered Magnetic Memory Structures	HPDC 11/23/05 Samsung 07/26/07	017281.0810 01961.0465		5649-2242
Sharma et al.	11/286,009	11/23/05	Multi-Layered Magnetic Memory Structures	HPDC 11/23/05 Samsung 07/26/07	017281.0828 01961.0343		5649-2243
Perner	11/286,861	11/03/05	Analog Preamplifier Calibration	HPDC 11/03/05 Samsung 07/26/07	017195.0971 01961.0576		5649-2244
Perner	11/287,705	11/03/05	Digital Current Source	HPDC 11/03/05 Samsung 07/26/07	017226.0959 01961.0261		5649-2245
Nickel	11/050,273	02/03/05	Method of Fabricating a Manganese Diffusion Barrier	HPDC 06/06/06 Samsung 07/26/07	016306.0539 01961.0337		5649-2247
Eaton	10/661,448	09/11/03	Increased Magnetic Memory Array Sizes and Operating Margins	HPDC 12/03/03 Samsung 07/26/07	014171.0302 01961.0624		5649-2248
Sharma	10/831,110	04/26/04	Data Input Device That Utilizes A Layer Of Magnetic Particles To Store Non-Volatile Input Data That Is Magnetically Coupled To An Underlying MRAM Array (As Amended)	HPDC 04/26/04 Samsung 07/26/07	015226.0350 01961.0531		5649-2249
Nickel	11/034,418	01/12/05	RF Field Heated Diodes for Providing Thermally Assisted Switching of Magnetic Memory Elements	HPDC 01/12/05 Samsung 07/26/07	016180.0951 01961.0001		5649-2250